

KSR1205

NPN EPITAXIAL SILICON TRANSISTOR

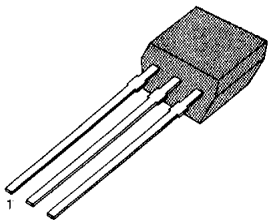
SWITCHING APPLICATION (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ( $R_1=4.7k\Omega$ ,  $R_2=10k\Omega$ )
- Complement to KSR2205

ABSOLUTE MAXIMUM RATINGS ( $T_A=25^{\circ}C$ )

| Characteristic            | Symbol    | Rating    | Unit        |
|---------------------------|-----------|-----------|-------------|
| Collector-Base Voltage    | $V_{CBO}$ | 50        | V           |
| Collector-Emitter Voltage | $V_{CEO}$ | 50        | V           |
| Emitter-Base Voltage      | $V_{EBO}$ | 10        | V           |
| Collector Current         | $I_C$     | 100       | mA          |
| Collector Dissipation     | $P_C$     | 300       | mW          |
| Junction Temperature      | $T_J$     | 150       | $^{\circ}C$ |
| Storage Temperature       | $T_{STG}$ | -55 ~ 150 | $^{\circ}C$ |

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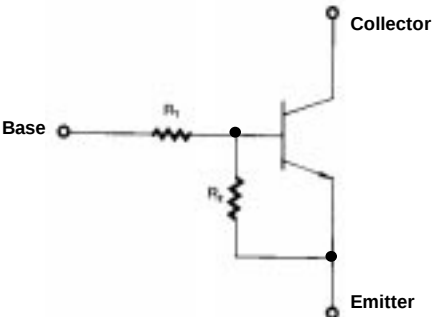


1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}C$ )

| Characteristic                       | Symbol        | Test Conditions                      | Min  | Typ  | Max  | Unit      |
|--------------------------------------|---------------|--------------------------------------|------|------|------|-----------|
| Collector-Base Breakdown Voltage     | $BV_{CBO}$    | $I_C=10\mu A$ , $I_E=0$              | 50   |      |      | V         |
| Collector-Emitter Breakdown Voltage  | $BV_{CEO}$    | $I_C=100\mu A$ , $I_B=0$             | 50   |      |      | V         |
| Collector Cut-off Current            | $I_{CBO}$     | $V_{CB}=40V$ , $I_E=0$               |      |      | 0.1  | $\mu A$   |
| DC Current Gain                      | $h_{FE}$      | $V_{CE}=5V$ , $I_C=5mA$              | 30   |      |      |           |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=10mA$ , $I_B=0.5mA$             |      |      | 0.3  | V         |
| Output Capacitance                   | $C_{OB}$      | $V_{CB}=10V$ , $I_E=0$<br>$f=1.0MHz$ |      | 3.7  |      | pF        |
| Current Gain-Bandwidth Product       | $f_T$         | $V_{CE}=10mA$ , $I_C=5mA$            |      | 250  |      | MHz       |
| Input Off Voltage                    | $V_i(off)$    | $V_{CE}=5V$ , $I_C=100\mu A$         | 0.3  |      |      | V         |
| Input On Voltage                     | $V_i(on)$     | $V_{CE}=0.3V$ , $I_C=20mA$           |      |      | 2.5  | V         |
| Input Resistor                       | $R_1$         |                                      | 3.2  | 4.7  | 6.2  | $k\Omega$ |
| Resistor Ratio                       | $R_1/R_2$     |                                      | 0.42 | 0.47 | 0.52 |           |

Equivalent Circuit



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